

ANGI019021-P43

L-band matched GaN Device

Features:

Frequency: $1.9 \sim 2.1 \text{GHz}$ Saturated Output Power: $P_{\text{sat}} \ge 43 \text{dBm}$ PowerGain: Gain $\ge 12 \text{dB}$ Add-Efficiency: PAE $\ge 50\%$ Port Matching: $Z_{\text{in}}/Z_{\text{out}} = 50\Omega$

Description:

ANGI019021-P43 is an internal matching GaN device, which adopts advanced co-planar internal matching MCM and thin film circuit technology. The typical working frequency range is 1.9~2.1GHz. This device can be used in different RF/Microwave system and subsystem.

The high output power level, high efficiency and wide operating temperature range can make application very flexible.

Maximun Ratings (TC=25°C, Not recommended working under this condition):

	Symbol	Value	Unit
Voltage between source and drain	Vds	40	V
Voltage between gate and source	V _{GS}	-5	V
Storage Temperature Range	Tstg	-65 to +175	°C
Drain and Source Channel Temperature	Tch	175	°C

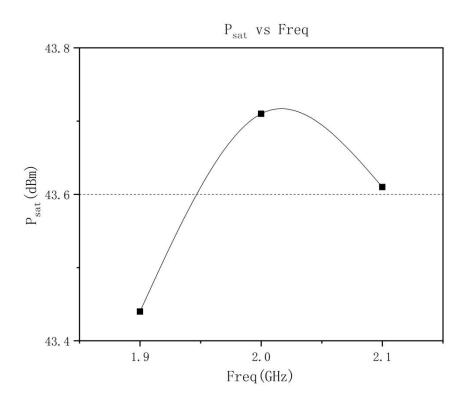
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Electrical Characteristics:

			Value			
	Symbol	Test condition	Min	Тур	Max	Unit
Drain Current	ldsr	Vds=28V CW. Pin: 31dBm Freq: 1.9~2.1GHz	-	1.3	-	А
Saturated Output Power	Psat		43	-	-	dBm
Gain	Gp		12	-	-	dB
Add-Efficiency	PAE		50	-	-	%
Gain Flatness	ΔG		-0.8	-	+0.8	dB

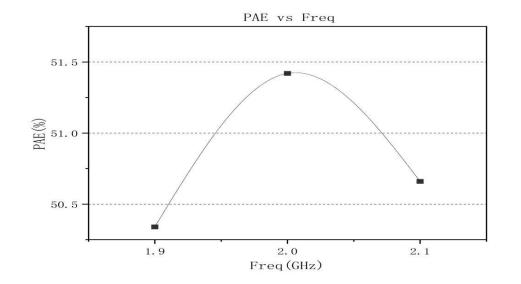
Typical Curve:



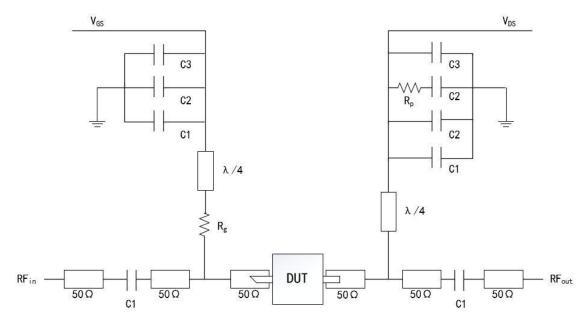
If you need more detailed product information, please contact our marketing personnel or designers. Contact: Peter.Zhang Email: peter.zhang@anserrf.com

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Application Circuit:



DUT: Device to be tested

C1:20pF	R _p :51Ω
C2:1000pF	R _G :15Ω

C3:100uF

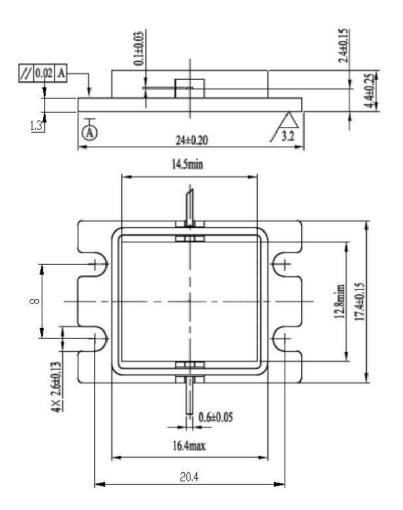
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ESD Level:



Outline:



Precautions for use:

- Pay attention to drying transportation and storage.
- Pay attention to anti-static during chip use and assembly, and wear grounding anti-static bracelet.
- When powering up, first apply grid power then add leakage.

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